



YJQ200P10AJ

P-Channel Enhancement Mode Field Effect Transistor

Product Summary

V_{DS}	-100V
I_D	-8A
$R_{DS(ON)}$ (at $V_{GS}=-10V$)	200m
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	235m
100% EAS Tested	
100% V_{DS} Tested	

General Description



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Electrical Characteristics (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
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S



YJQ200P10AJ

Typical Electrical 50.57WBT/F5 10.56f1 0 0 1 0.9420.4Tm0 g0 G[2]JT3cfica



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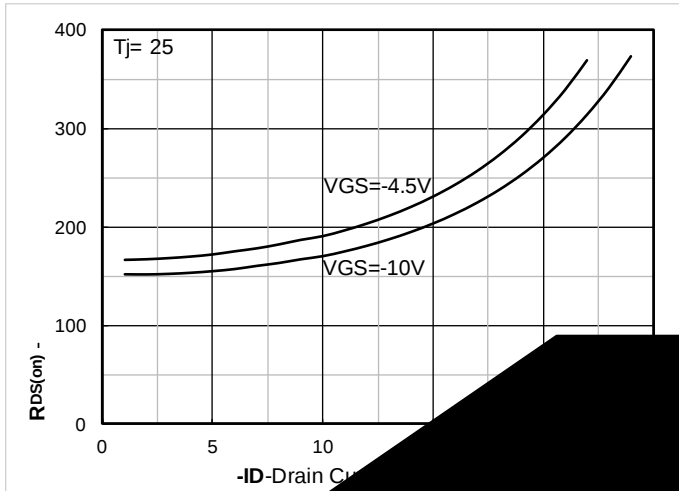


Figure 7. On-resistance

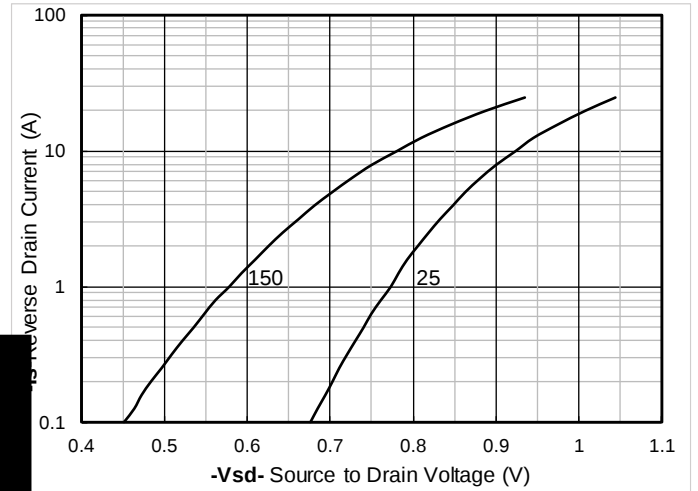


Figure 8. Reverse current

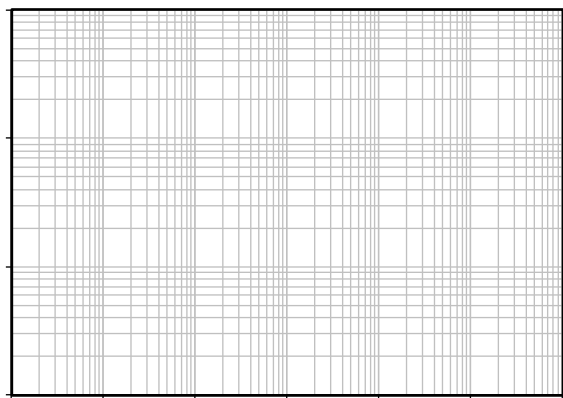


Figure 13. Maximum Transient Thermal Impedance

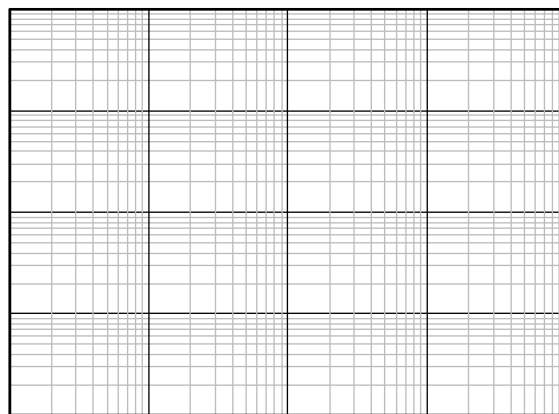
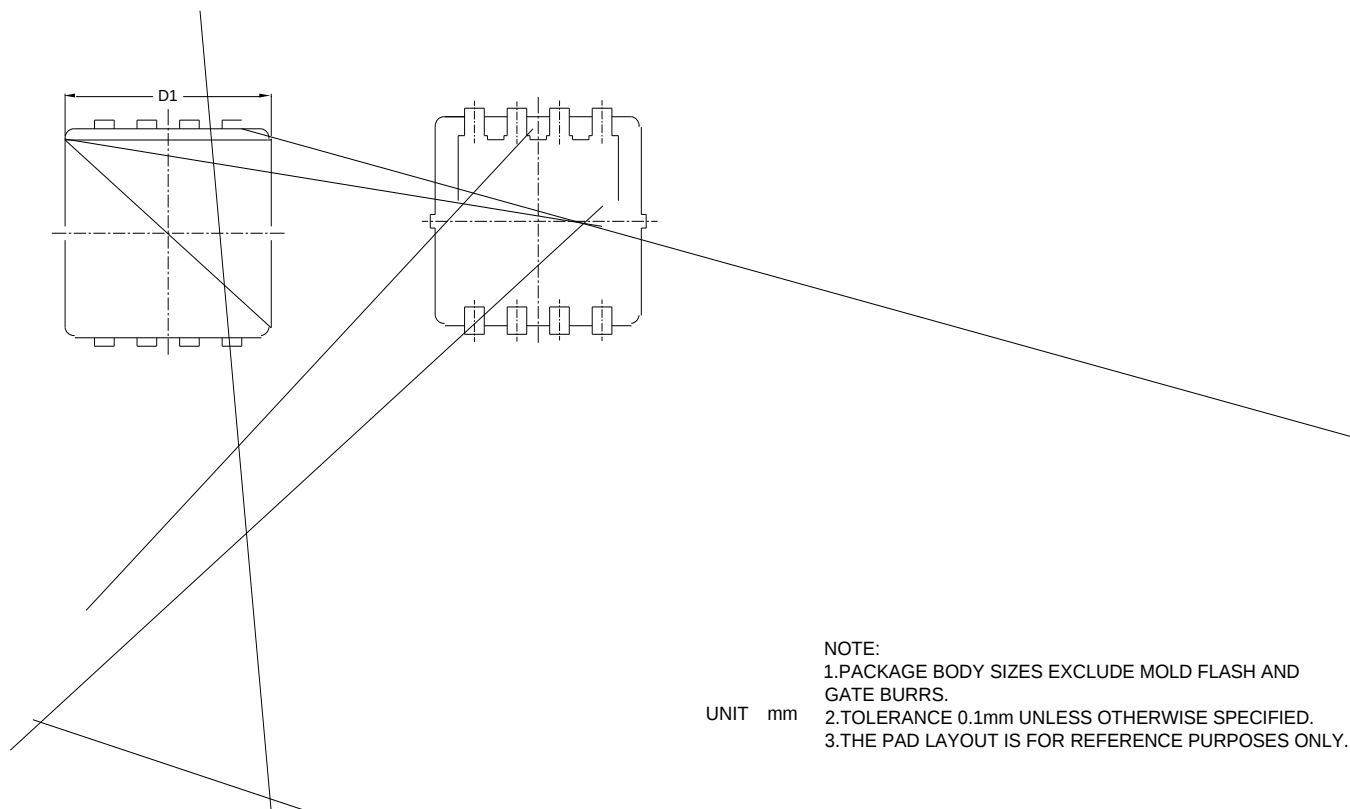


Figure 14. Safe Operation Area



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PDFN3333-8L-B-0.75MM Package information





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